

LED CHIP C940-55P

SPECIFICATION OF LED CHIP  
C940-55P  
[INFRARED]

1) Commodity Type and Physical Characteristics.

- 1. Material GaAlAs/GaAs
- 2. Electrode Top Side P (anode) side : Au Alloy  
Bottom Side N (cathode) side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.15	1.25	V
Forward Voltage	Vf	If=50mA		1.23	1.35	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.0	3.5		mW
Peak Wavelength	λ P	If=20mA	930	940	955	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		50		nm
RiseTime	tr	If=20mA		1000		ns
FallTime	tf	If=20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

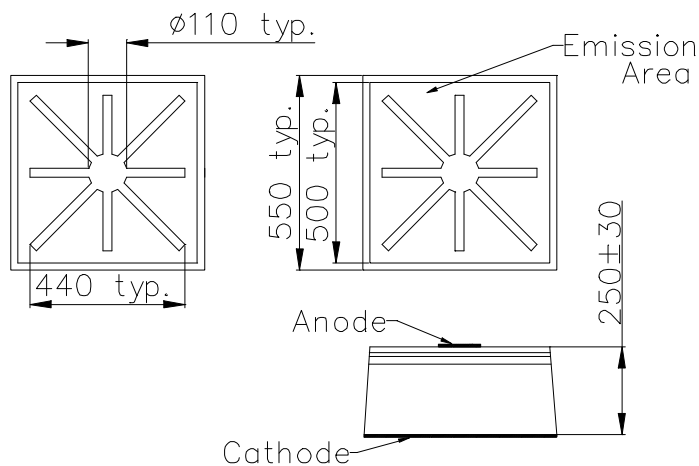


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area